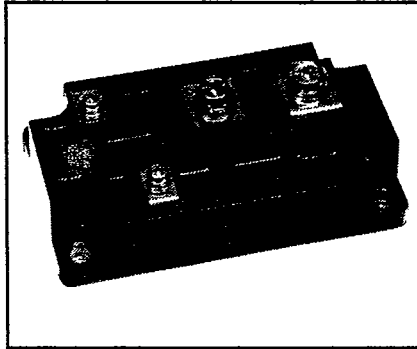
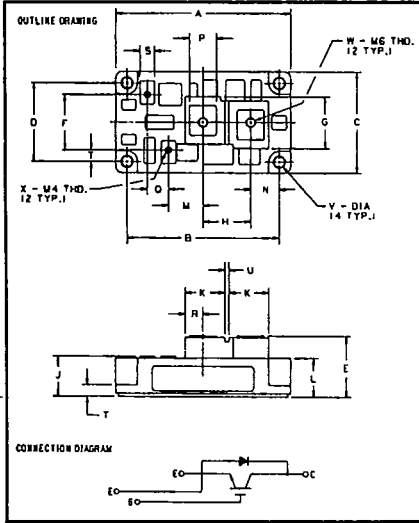




IS626030 - T-39-31

Powerex, Inc., Hillis Street, Youngwood, Pennsylvania 15697 (412) 925-7272
 Powerex, Europe, S.A. 428 Avenue G. Durand, BP107, 72003 Le Mans, France (43) 41.14.14

**Single IGBTMOD™
 Power Module**
 300 Amperes/600 Volts



**IS626030
 Single IGBTMOD™ Power Module**
 300 Amperes/600 Volts

**IS626030
 Outline Drawing**

Dimension	Inches	Millimeters
A	4.21	107.0
B	3.661±.010	93.00±0.25
C	2.44	62.0
D	1.890±.010	48.00±0.25
E	1.42 Max.	36.0 Max.
F	1.34	34.0
G	1.18	30.0
H	1.14	29.0
J	.98 Max.	25.0 Max.
K	.94	24.0
L	.93	23.5
M	.83	21.0
N	.69	17.5
P	.63	16.0
Q	.51	13.0
R	.43	11.0
S	.35	9.0
T	.28	7.0
U	.12	3.0
V	.26 Dia.	Dia. 6.5
W	M6 Metric	M6
X	M4 Metric	M4

Description

Powerex IGBTMOD™ Modules are designed for use in switching applications. Each module consists of one IGBT Transistor in a single configuration, with a reverse-connected super-fast recovery free wheel diode. All components and interconnects are isolated from the heat sinking baseplate, offering simplified system assembly and thermal management.

Features:

- Low Drive Power
- Low $V_{CE(sat)}$
- Discrete Super-Fast Recovery (150ns) Free Wheel Diode
- High Frequency Operation (15-20kHz)
- Isolated Base Plate for Easy Heat Sinking

Applications:

- AC Motor Control
- Motion/Servo Control
- UPS
- Welding Power Supplies
- Laser Power Supplies

Ordering Information

Example: Select the complete eight digit part module number you desire from the table below -i.e. IS626030 is a 600V (V_{CES}), 300 Ampere Single IGBTMOD™ Power Module.

Type	V_{CES} Volts (x10)	Current Rating Amperes (x10)
IS62	60	30



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Absolute Maximum Ratings, $T_j = 25^\circ\text{C}$ unless otherwise specified

Ratings	Symbol	IS626030	Units
Junction Temperature	T_j	-40 to 150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-40 to 125	$^\circ\text{C}$
Collector-Emitter Voltage (G-E SHORT)	V_{CES}	600	Volts
Gate-Emitter Voltage	V_{GES}	± 20	Volts
Collector Current	I_C	300	Amperes
Peak Collector Current	I_{CM}	600*	Amperes
Diode Forward Current	I_{FM}	300	Amperes
Diode Forward Surge Current	I_{FM}	600*	Amperes
Power Dissipation	P_d	1100	Watts
Max. Mounting Torque M6 Terminal Screws	—	26	in.-lb.
Max. Mounting Torque M6 Mounting Screws	—	26	in.-lb.
Module Weight (Typical)	—	400	Grams
V isolation	V_{RMS}	2500	Volts

* Pulse width and repetition rate should be such that device junction temperature does not exceed the device rating.

Static Electrical Characteristics, $T_j = 25^\circ\text{C}$ unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Collector-Cutoff Current	I_{CES}	$V_{CE} = V_{CES}, V_{GE} = 0V$	—	—	1.0	mA
Gate Leakage Current	I_{GES}	$V_{GE} = V_{GES}, V_{CE} = 0V$	—	—	0.5	μA
Gate-Emitter Threshold Voltage	$V_{GE(th)}$	$I_C = 30\text{mA}, V_{CE} = 10V$	3.0	4.0	6.0	Volts
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 300A, V_{GE} = 15V$	—	3.0	5.0**	Volts
		$I_C = 300A, V_{GE} = 15V, T_j = 150^\circ\text{C}$	—	3.2	**	Volts
Total Gate Charge	Q_G	$V_{CC} = 300V, I_C = 300A, V_{GS} = 15V$	—	1100	—	nC
Diode Forward Voltage	V_{FM}	$I_C = -300A, V_{GS} = 0V$	—	—	2.5	Volts

** Pulse width and repetition rate should be such that device junction temperature rise is negligible.

Dynamic Electrical Characteristics, $T_j = 25^\circ\text{C}$ unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Input Capacitance	C_{iss}		—	—	33000	pF
Output Capacitance	C_{oss}	$V_{GE} = 0V, V_{CE} = 10V, f = 1\text{MHz}$	—	—	8100	pF
Reverse Transfer Capacitance	C_{res}		—	—	810	pF
Resistive	Turn-on Delay Time		—	—	1100	ns
	Rise Time	$V_{CC} = 300V, I_C = 300A,$	—	—	800	ns
Load	Turn-off Delay Time	$V_{GE1} = V_{GE2} = 15V, R_G = 8.3\Omega$	—	—	800	ns
Switch Times	Fall Time		—	—	800	ns
Diode Reverse Recovery Time	t_{rr}	$I_E = 300A, di_E/dt = -300A/\mu\text{s}$	—	—	200	ns
Diode Reverse Recovery Charge	Q_{rr}	$I_E = 300A, di_E/dt = -300A/\mu\text{s}$	—	4.0	—	μC

Thermal and Mechanical Characteristics, $T_j = 25^\circ\text{C}$ unless otherwise specified

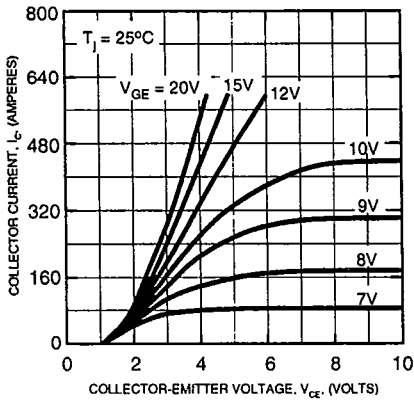
Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Thermal Resistance, Junction to Case	$R_{th(j-c)}$	Per IGBT	—	—	0.11	$^\circ\text{C/W}$
Thermal Resistance, Junction to Case	$R_{th(j-c)}$	Per Free Wheel Diode	—	—	0.24	$^\circ\text{C/W}$
Contact Thermal Resistance	$R_{th(c-t)}$	Per Module	—	—	—	$^\circ\text{C/W}$



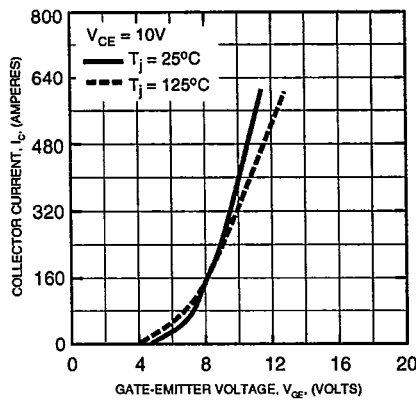
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IS626030
 Single IGBTMOD™ Power Module
 300 Amperes/600 Volts

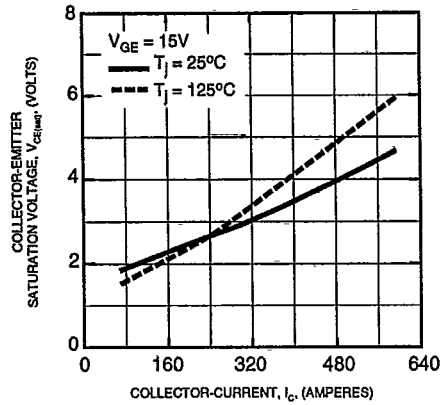
OUTPUT CHARACTERISTICS (TYPICAL)



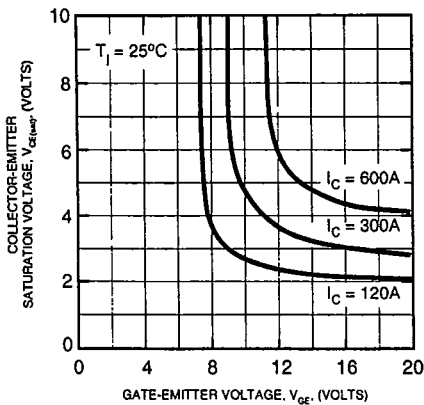
TRANSFER CHARACTERISTICS (TYPICAL)



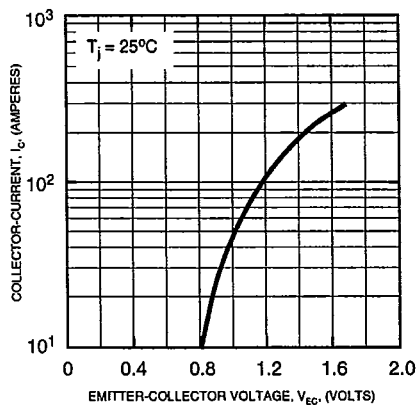
COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS (TYPICAL)



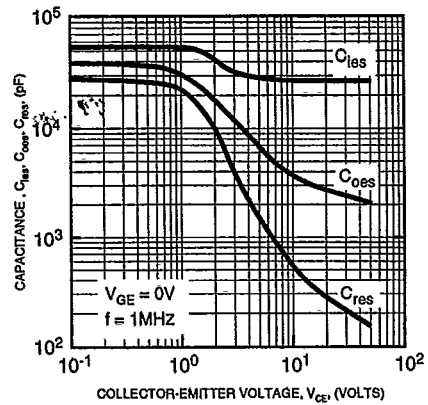
COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS (TYPICAL)



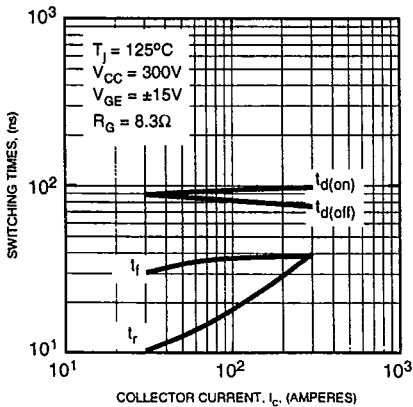
FREE-WHEEL DIODE FORWARD CHARACTERISTICS (TYPICAL)



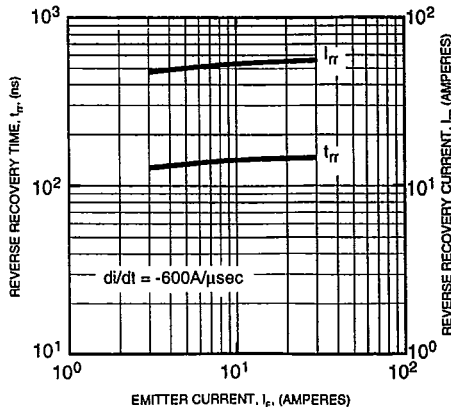
CAPACITANCE VS. V_{ce} (TYPICAL)



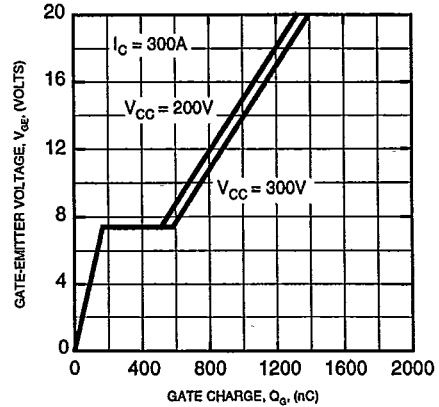
HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)



REVERSE RECOVERY CHARACTERISTICS (TYPICAL)



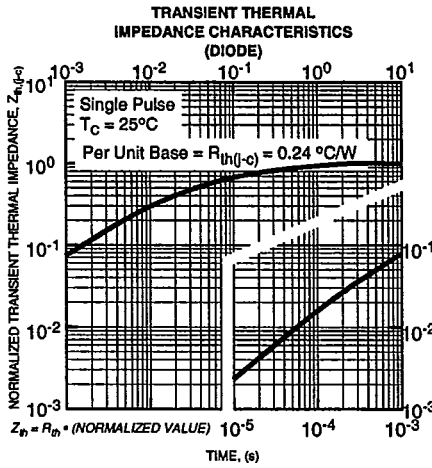
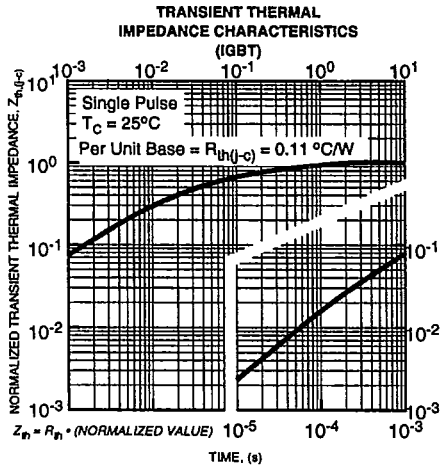
GATE CHARGE, V_{ge}



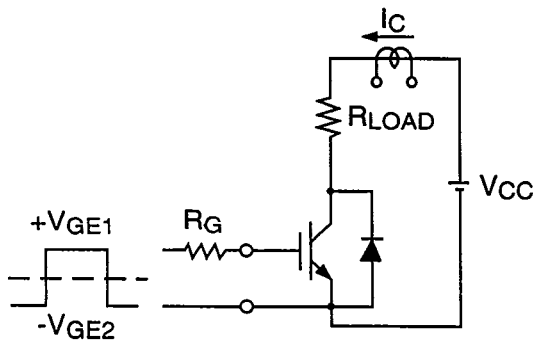


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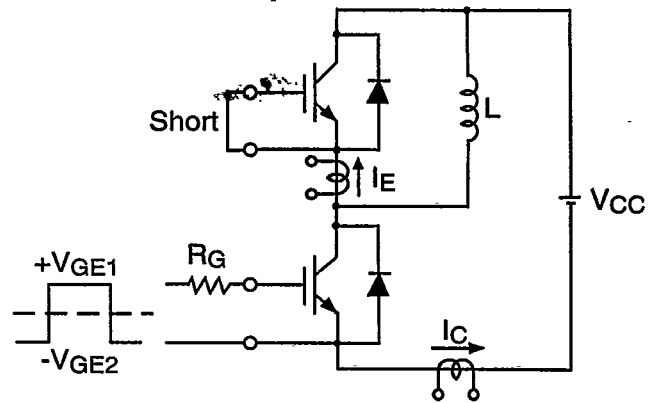
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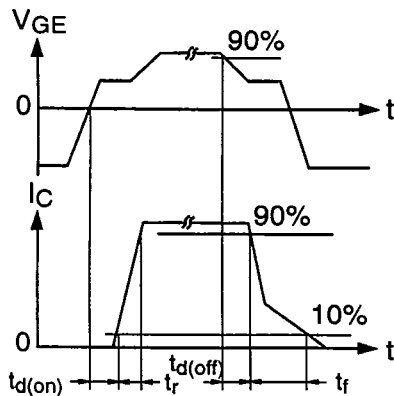
SWITCHING TIME TEST CIRCUITS & WAVEFORMS



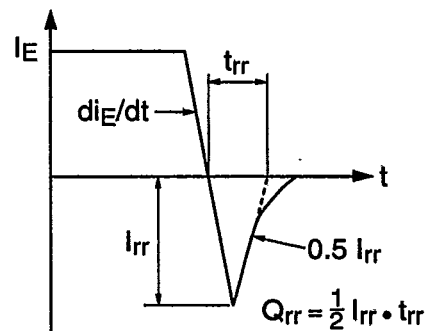
Resistance Load Switching Test Circuit



Half-Bridge Switching Test Circuit



Switching Time Test Waveforms



trr, Qrr Waveforms